

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An open-drain N-channel MOSFET comprising:
a drain region formed of an N-type semiconductor layer;
a P-type impurity diffusion layer formed within the drain region;
two high-concentration N-type impurity diffusion layers formed within the drain region
so as to sandwich the P-type impurity diffusion layer;
a low-concentration N-type impurity diffusion region formed in contact with the drain
region; and
a drain electrode connected to the P-type impurity diffusion layer and to the two high-
concentration N-type impurity diffusion layers.

2. (Currently Amended) A semiconductor integrated circuit device comprising:
an output circuit,
wherein the output circuit comprises:
an open-drain N-channel MOSFET; and
an output terminal connected to a drain of the open-drain N-channel MOSFET,
wherein the open-drain N-channel MOSFET comprises:
a drain region formed of an N-type semiconductor layer;
a P-type impurity diffusion layer formed within the drain region;
two high-concentration N-type impurity diffusion layers formed within the drain
region so as to sandwich the P-type impurity diffusion layer;

a low-concentration N-type impurity diffusion region formed in contact with the drain region; and

a drain electrode connected to the P-type impurity diffusion layer and to the two high-concentration N-type impurity diffusion layers.

3. (Currently Amended) A The semiconductor integrated circuit device as claimed in claim 2,

wherein there are provided a plurality of the output circuit.

4. (Currently Amended) A The semiconductor integrated circuit device as claimed in claim 3,

wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET each have, as seen in a plan view, a substantially circular shape or a substantially regular-polygonal shape with four or more sides, and gates of the open-drain N-channel MOSFET are formed in a net-like pattern.

5. (Currently Amended) A The semiconductor integrated circuit device as claimed in claim 3,

wherein the drain region and a source region of the open-drain N-channel MOSFET are formed in a pattern like teeth of a comb.

6. (Currently Amended) A The A semiconductor integrated circuit device as claimed in claim 3,

wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET have, as seen in a plan view, different shapes.

7. (Currently Amended) A The A semiconductor integrated circuit device as claimed in claim 3,

wherein a peripheral portion of the drain region of the open-drain N-channel MOSFET and a peripheral portion of a source region of the open-drain N-channel MOSFET each have, as seen in a plan view, a substantially circular shape or a substantially regular-polygonal shape with four or more sides, and gates of the open-drain N-channel MOSFET are formed in a net-like pattern,

wherein the drain region and the source region of the open-drain N-channel MOSFET are formed in a pattern like teeth of a comb, and

wherein the peripheral portion of the drain region of the open-drain N-channel MOSFET and the peripheral portion of the source region of the open-drain N-channel MOSFET have, as seen in a plan view, different shapes.